

**1-Line 3.3V Bi-directional TVS Diode**

**Description**

The PESDR0361D3 is a 3.3V bi-direction TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR0361D3 has a low capacitance with a typical value at 1.0pF, and complies with the IEC 61000-4-2(ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make PESDR0361D3 an ideal choice to protect cellphone, wireless systems, and communication equipment.

**Features**

- 350W peak pulse power (8/20µs)
- Ultra low capacitance: 1.0pF typical
- Ultra low leakage: nA level
- Low operating voltage: 3.3 V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±30kV
  - IEC 61000-4-4 (EFT) 40A (5/50ns)
  - IEC 61000-4-5 (Lightning) 20A (8/20µs)
- RoHS Compliant

**Mechanical Characteristics**

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Marking Information: See Below

**Applications**

- Ethernet - 10/100/1000 Base T
- Cellular Phones
- Handheld - Wireless Systems
- Personal Digital Assistant (PDA)
- USB Interface

**Marking Information**

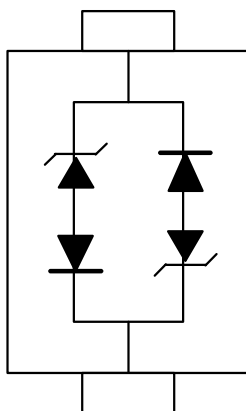


**3B** = Device Marking Code

**Ordering Information**

Part Number	Shipping	Reel Size
PESDR0361D3	3000/Tape &Reel	7 inch

**Dimensions and Pin Configuration**



Circuit and Pin Schematic

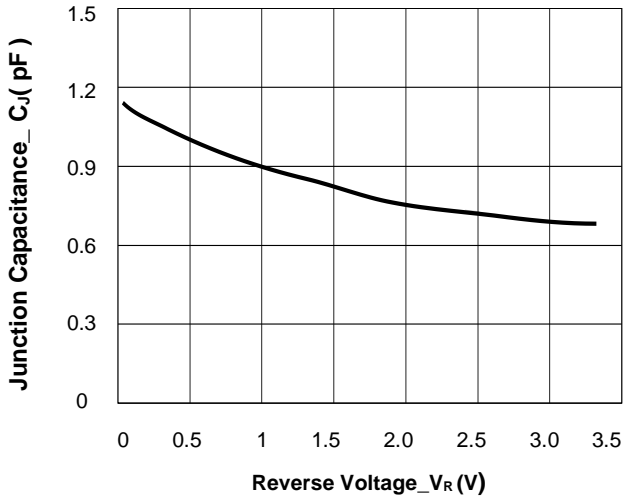
**Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 $\mu\text{s}$ )	$P_{PK}$	350	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	$I_{PP}$	20	A
ESD per IEC 61000-4-2 (Air)	$V_{ESD}$	$\pm 30$	kV
ESD per IEC 61000-4-2 (Contact)		$\pm 30$	kV
Operating Temperature Range	$T_{OP}$	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to +150	$^\circ\text{C}$

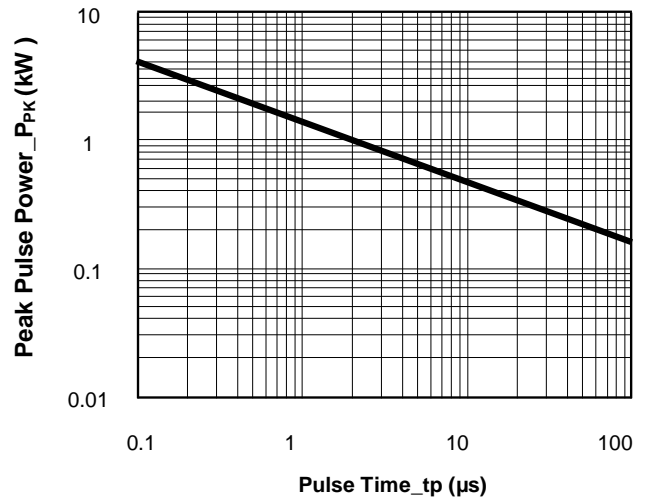
**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	$V_{RWM}$			3.3	V	
Reverse Breakdown Voltage	$V_{BR}$	4		7	V	$I_T = 1\text{mA}$
Reverse Leakage Current	$I_R$			20	nA	$V_{RWM} = 3.3\text{ V}$
Clamping Voltage	$V_C$		8	11	V	$I_{PP} = 1\text{A}$ (8/20 $\mu\text{s}$ pulse)
Clamping Voltage	$V_C$		16	19	V	$I_{PP} = 20\text{A}$ (8/20 $\mu\text{s}$ pulse)
ESD Clamping Voltage	$V_C$		8.5			$I_{PP} = 4\text{A}$ ( $t_p = 0.2/100\text{ns}$ )
ESD Clamping Voltage	$V_C$		12.0			$I_{PP} = 16\text{A}$ ( $t_p = 0.2/100\text{ns}$ )
Junction Capacitance	$C_J$		1.0	2.0	pF	$V_R = 0\text{V}$ , $f = 1\text{MHz}$

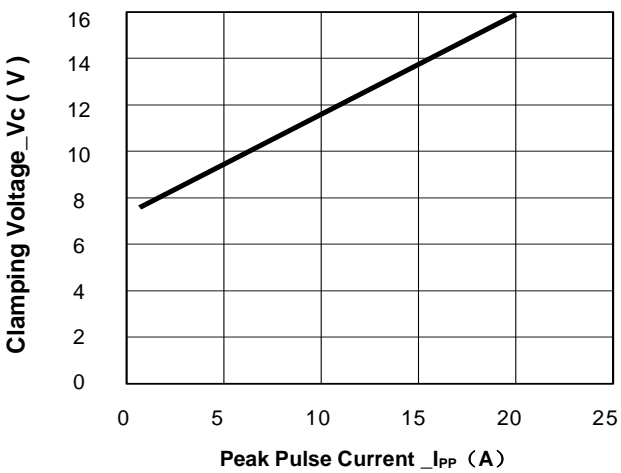
**Typical Performance Characteristics (T<sub>A</sub>=25°C unless otherwise Specified)**



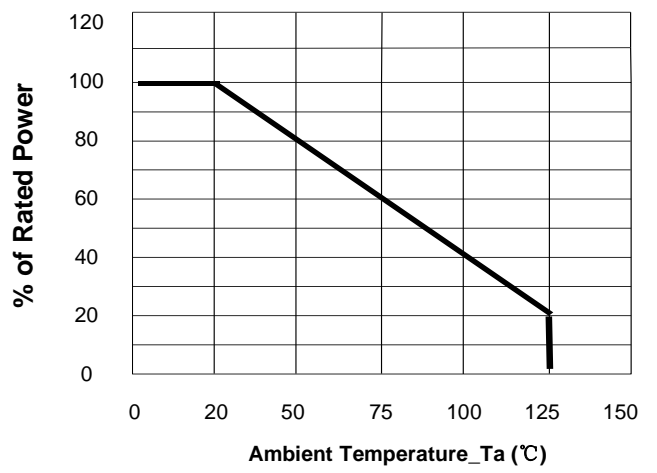
**Junction Capacitance vs. Reverse Voltage**



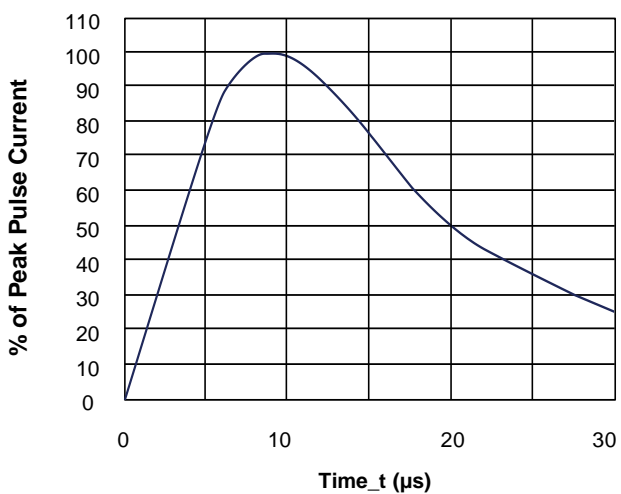
**Peak Pulse Power vs. Pulse Time**



**Clamping Voltage vs. Peak Pulse Current**

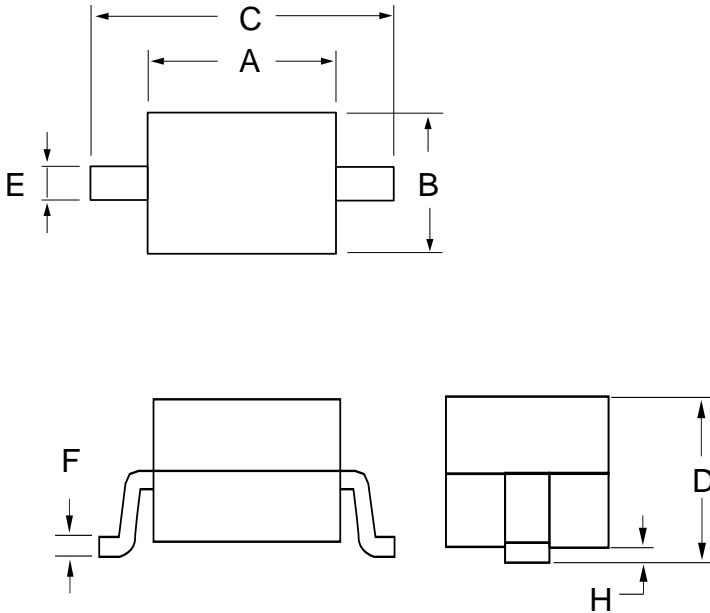


**Power Derating Curve**



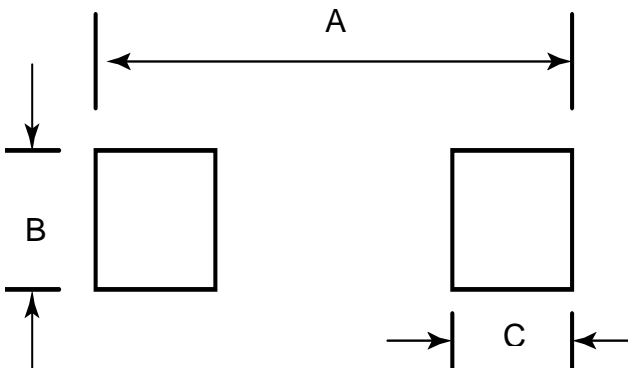
**8/20μs Pulse Waveform**

**SOD-323 Package Outline Drawing**



SYM	DIMENSIONS				
	MILLIMETERS			INCHES	
	MIN	NOM	MAX	MIN	MAX
A	1.50	1.65	1.80	0.060	0.071
B	1.20	1.30	1.40	0.045	0.054
C	2.30	2.50	2.70	0.090	0.107
D	-		1.10	-	0.043
E	0.30		0.40	0.012	0.016
F	0.10		0.25	0.004	0.010
H	-		0.10	-	0.004

**Suggested Land Pattern**



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

单击下面可查看定价，库存，交付和生命周期等信息

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